



GP 2811

Attorney's Docket No.: 10417-039001 / F51-125462M/HW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Toshimitsu Taniguchi et al. Art Unit : 2811
Serial No. : 09/652,044 Examiner : Unknown
Filed : August 31, 2000
Title : SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING
THEREOF

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2-9-02
Payton

Commissioner for Patents
Washington, D.C. 20231

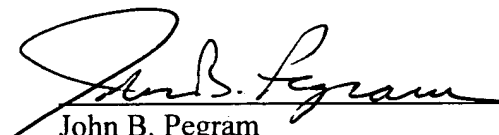
RESPONSE TO RESTRICTION REQUIREMENT

Responsive to the action mailed December 4, 2001, applicant elects the invention of Group II drawn to method and including claims 6-21. The election is made without traverse.

Please apply any charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,-

Date: December 18, 2001


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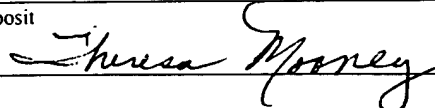
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December 18, 2001

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Theresa Mooney

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PRELIMINARY AMENDMENT

Prior to examination, please amend the application as follows:

In the specification:

Replace the paragraph beginning at page 8, line 21, with the following rewritten paragraph:

-- A method of manufacturing various MOS transistors composing the driver for driving a liquid crystal will be described below. The semiconductor of the present invention is applicable to various drivers such as a liquid crystal driver.--

Replace the paragraph beginning at page 9, line 22 to page 10, line 15, with the following rewritten paragraph:

--Next, a first low concentration N-type and P-type source/drain layers (hereinafter called an LN layer 10 and an LP layer 11) are formed using a resist film as a mask. That is, first, phosphorus ions for example are implanted into the superficial layer of the substrate at the acceleration voltage of approximately 120 KeV under the implantation condition of $8 \times 10^{12}/\text{cm}^2$ in a state that an area except an area where the LN layer is formed is covered with a resist film

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